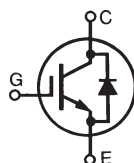


# XPT™ 650V GenX4™ w/ Sonic Diode

# IXXK110N65B4H1 IXXX110N65B4H1

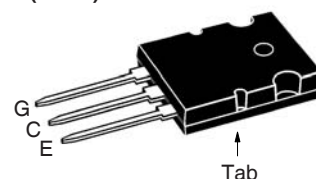
$V_{CES} = 650V$   
 $I_{C110} = 110A$   
 $V_{CE(sat)} \leq 2.10V$   
 $t_{fi(typ)} = 43ns$

Extreme Light Punch Through  
IGBT for 10-30kHz Switching

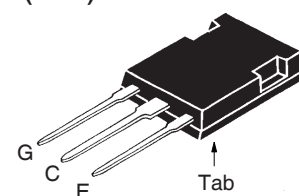


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	650	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	650	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ (Chip Capability)	250	A
$I_{LRMS}$	Terminal Current Limit	160	A
$I_{C110}$	$T_C = 110^\circ C$	110	A
$I_{F110}$	$T_C = 110^\circ C$	78	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	570	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 220$ @ $V_{CE} \leq V_{CES}$	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 360V$ , $T_J = 150^\circ C$ $R_G = 82\Omega$ , Non Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	880	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
$F_C$	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

TO-264 (IXXK)



PLUS247 (IXXX)



G = Gate                      E = Emitter  
 C = Collector                Tab = Collector

## Features

- Optimized for 10-30kHz Switching
- Square RBSOA
- Short Circuit Capability
- Anti-Parallel Sonic Diode
- High Current Handling Capability
- International Standard Packages

## Advantages

- High Power Density
- Low Gate Drive Requirement

## Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- High Frequency Power Inverters

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	4.0		6.5 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			25 $\mu A$ 3 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 110A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$	1.72 2.05		2.10 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1	30	52	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		5500	pF
$C_{oes}$			470	pF
$C_{res}$			80	pF
$Q_{g(on)}$	$I_C = 110\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		183	nC
$Q_{ge}$			32	nC
$Q_{gc}$			83	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 55\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		26	ns
$t_{ri}$			40	ns
$E_{on}$			2.20	mJ
$t_{d(off)}$			146	ns
$t_{fi}$			43	ns
$E_{off}$			1.05	1.70 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 55\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		25	ns
$t_{ri}$			40	ns
$E_{on}$			3.00	mJ
$t_{d(off)}$			140	ns
$t_{fi}$			110	ns
$E_{off}$			2.16	mJ
$R_{thJC}$				0.17 $^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

**Reverse Sonic Diode (FRD)**

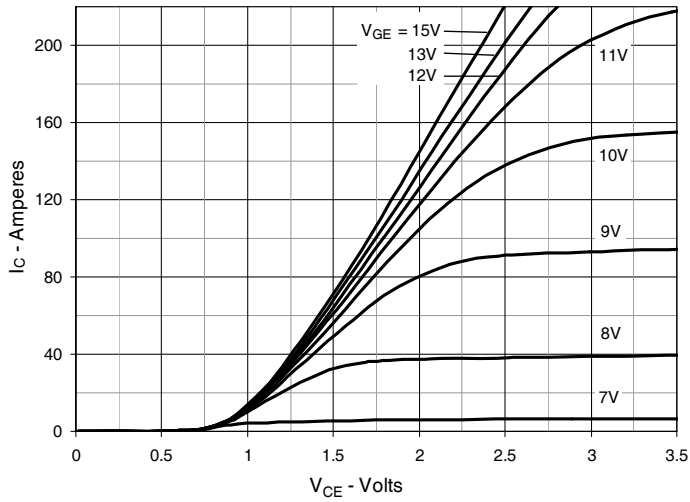
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 100\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 150^\circ\text{C}$		1.7 1.8	V V
$I_{RM}$	$I_F = 100\text{A}, V_{GE} = 0\text{V}, T_J = 150^\circ\text{C}$ $-di_F/dt = 1500\text{A}/\mu\text{s}, V_R = 300\text{V}$		95	A
$t_{rr}$			100	ns
$R_{thJC}$				0.38 $^\circ\text{C/W}$

**Notes:**

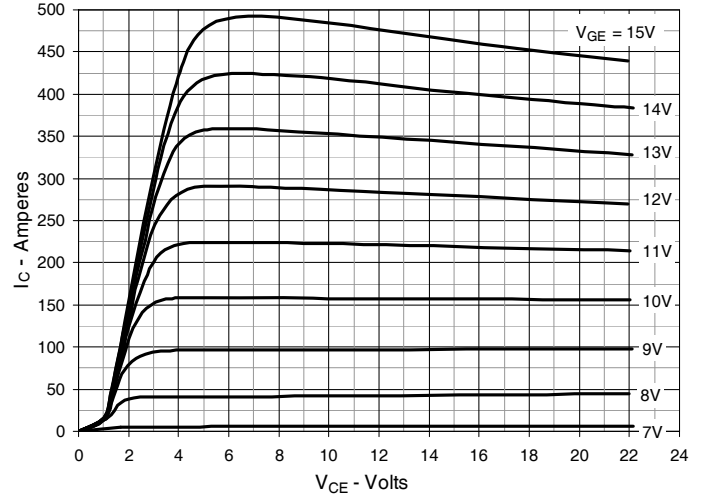
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (Clamp),  $T_J$  or  $R_G$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

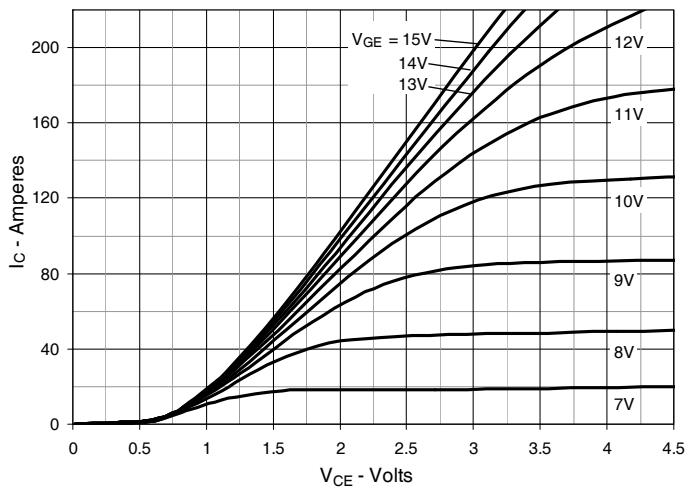
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



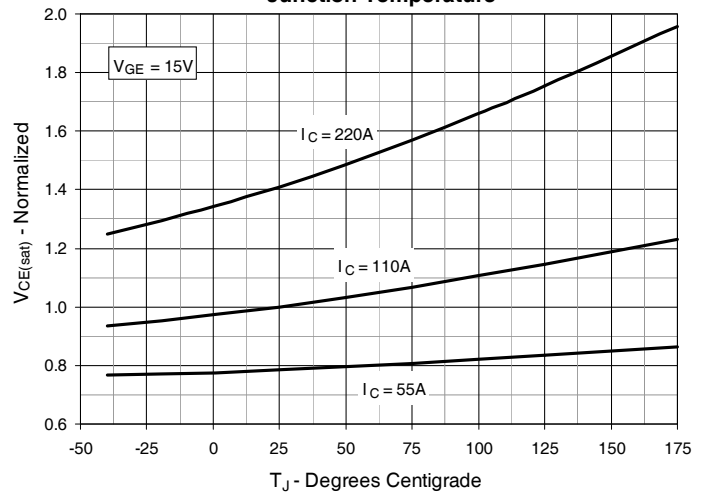
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



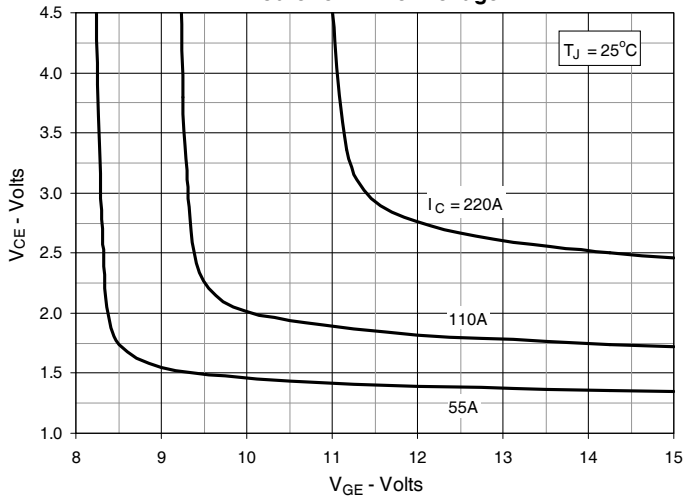
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



**Fig. 6. Input Admittance**

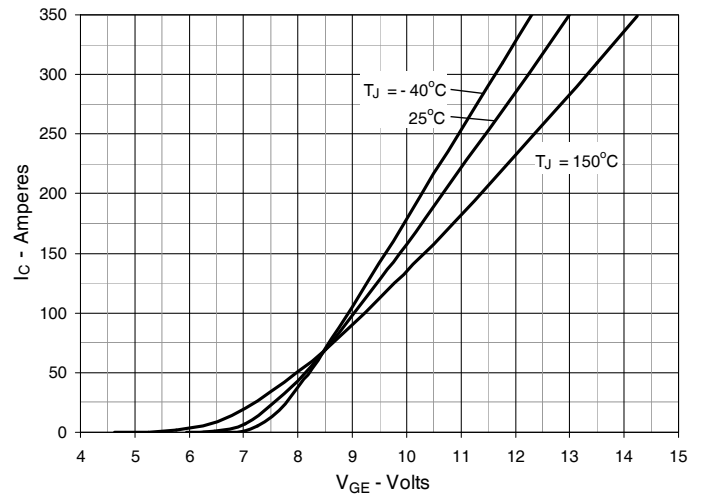


Fig. 7. Transconductance

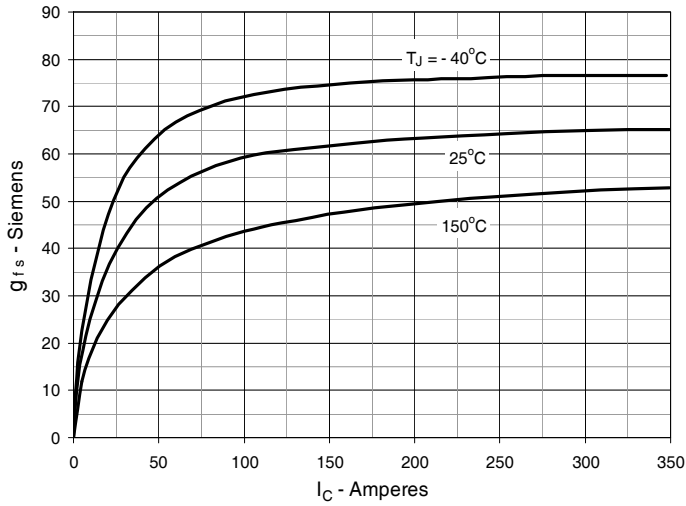


Fig. 8. Gate Charge

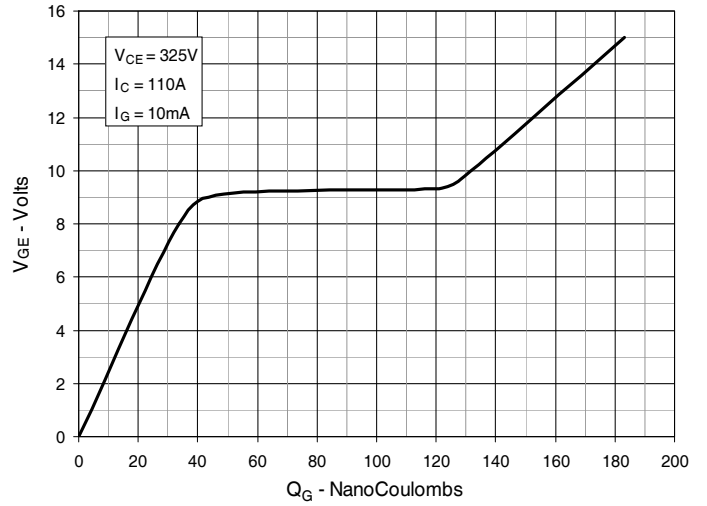


Fig. 9. Capacitance

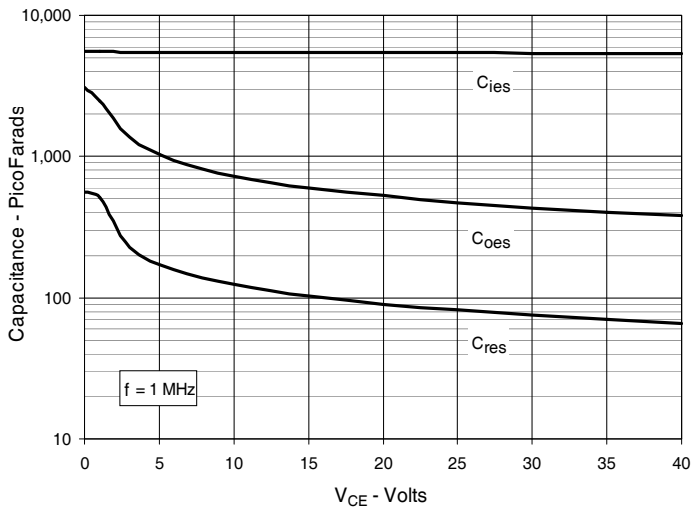


Fig. 10. Reverse-Bias Safe Operating Area

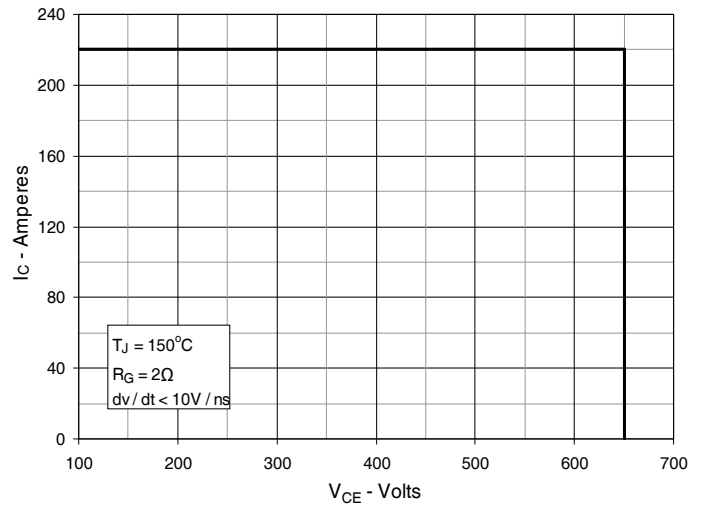
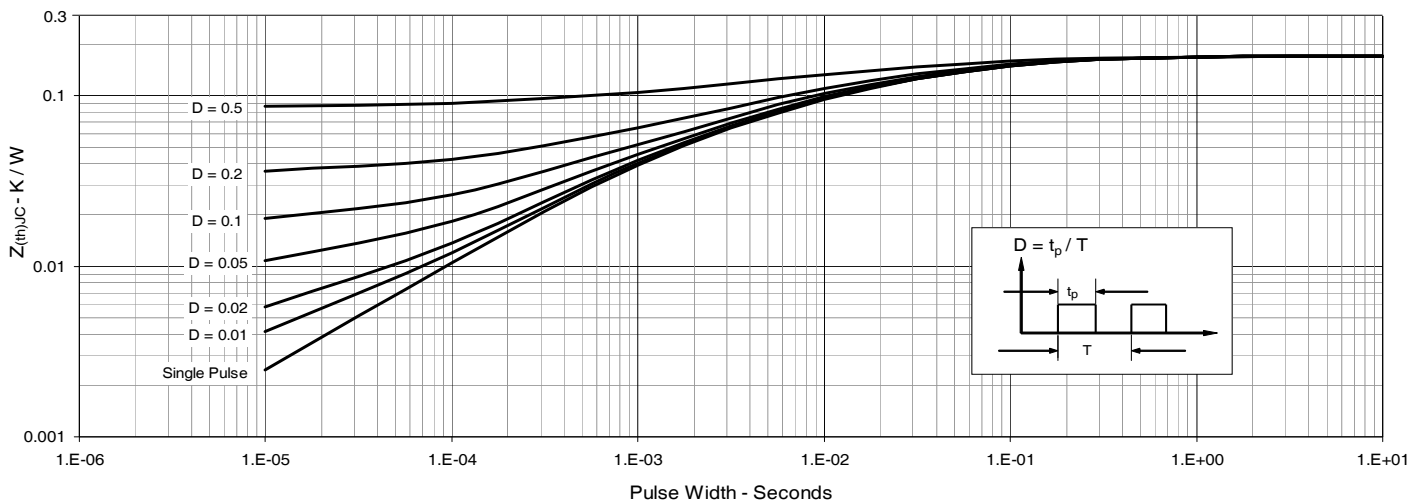
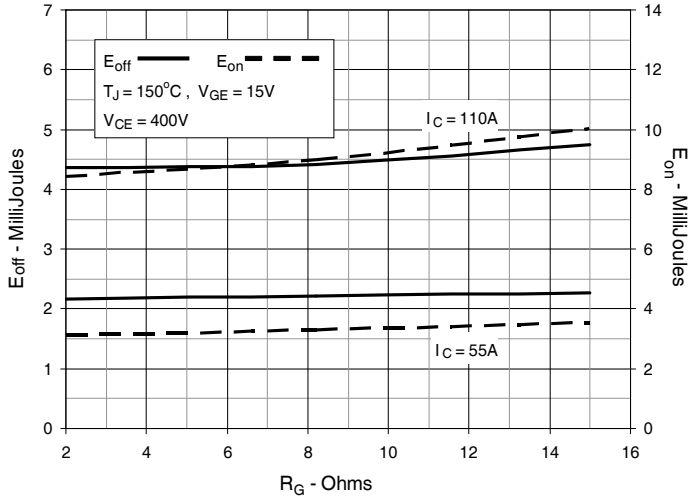


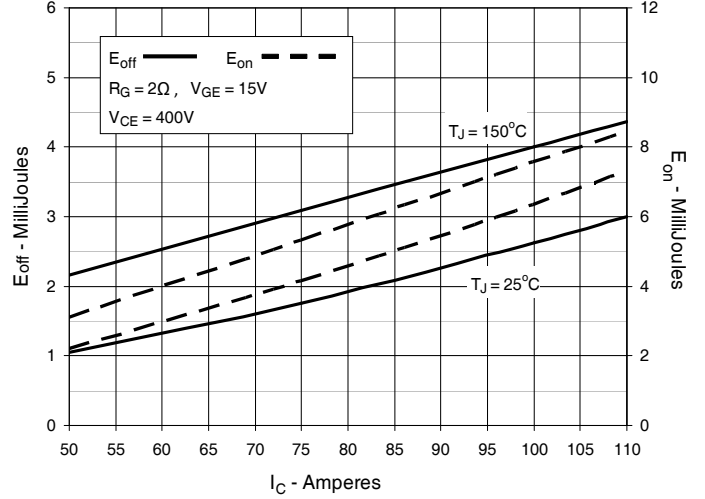
Fig. 11. Maximum Transient Thermal Impedance (IGBT)



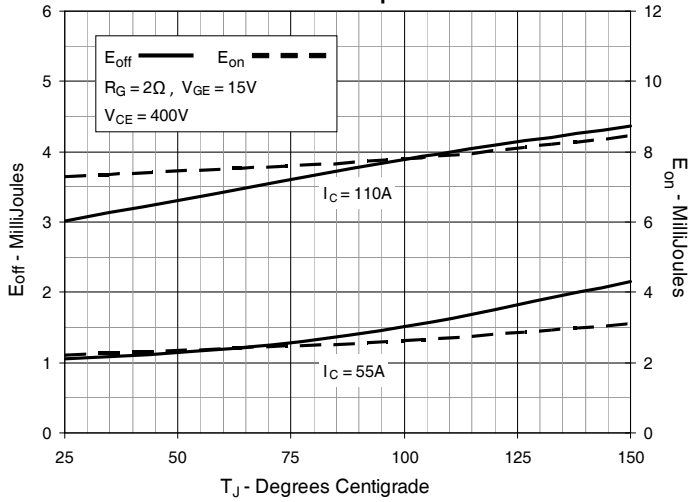
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



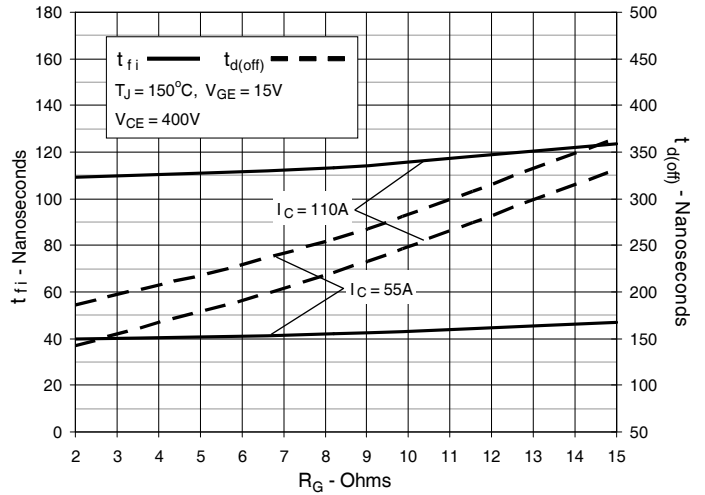
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



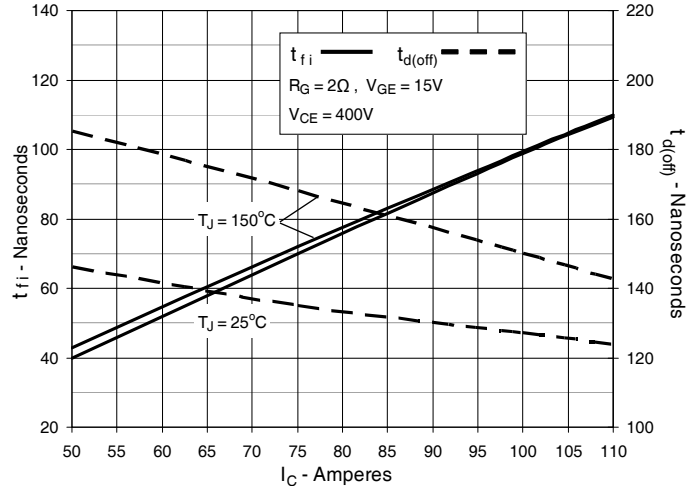
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



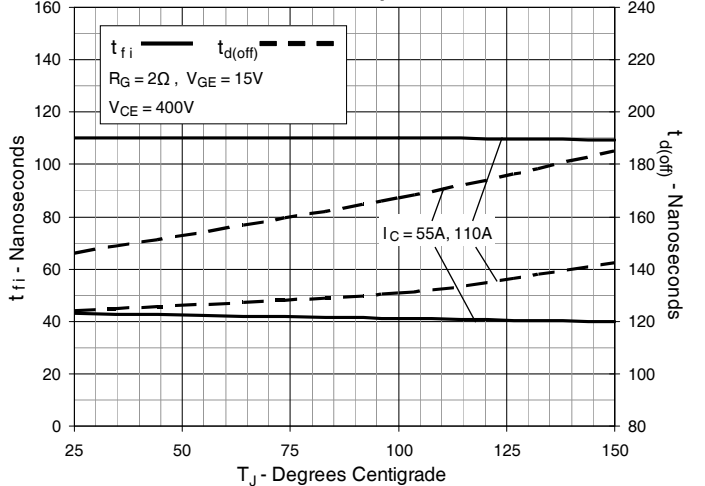
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



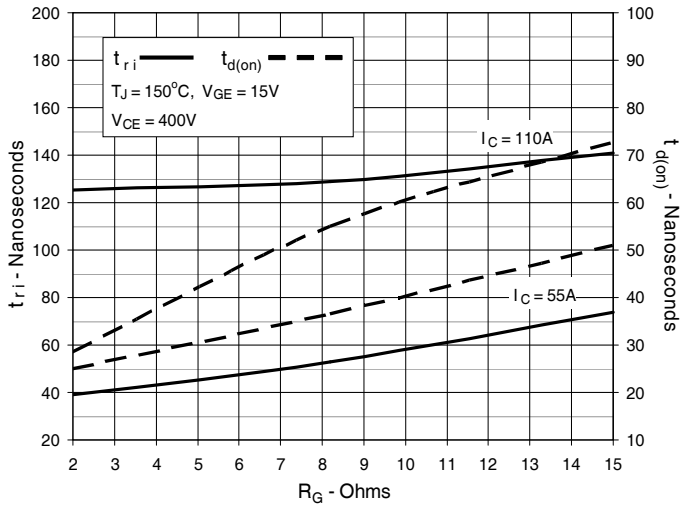
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



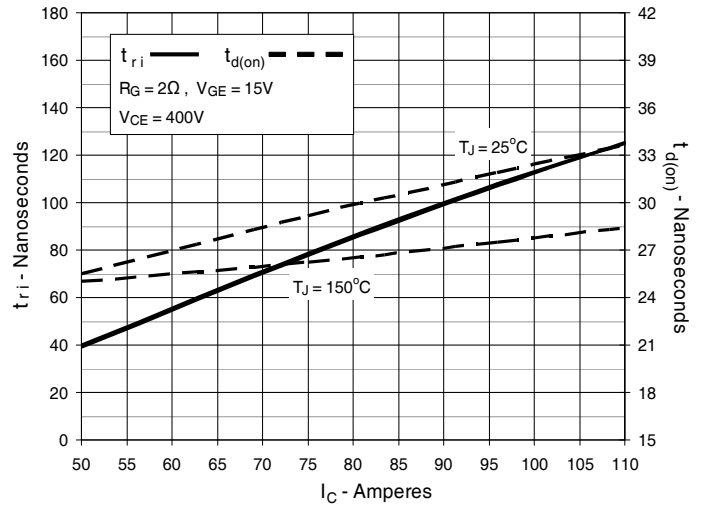
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**

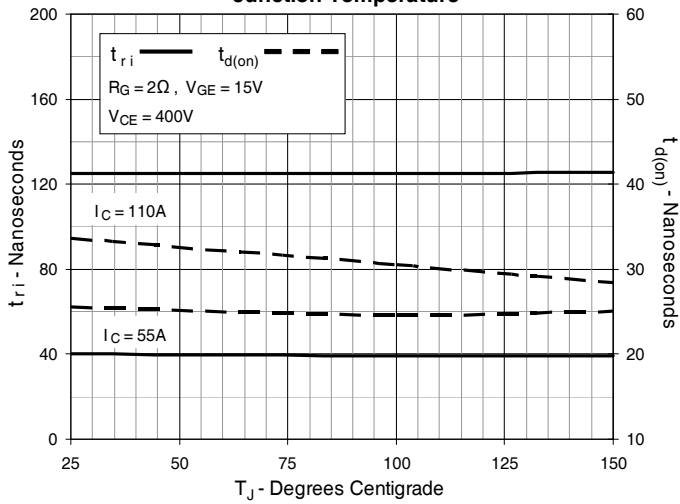


Fig. 21. Typ. Forward characteristics

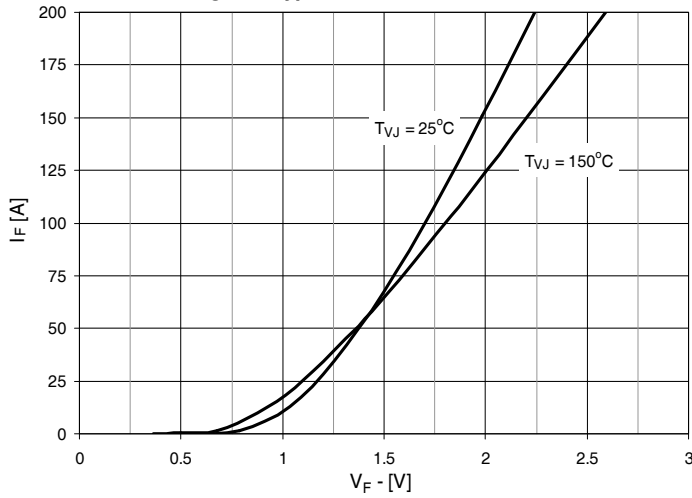


Fig. 22. Typ. Reverse Recovery Charge  $Q_{rr}$  vs.  $-di_F/dt$

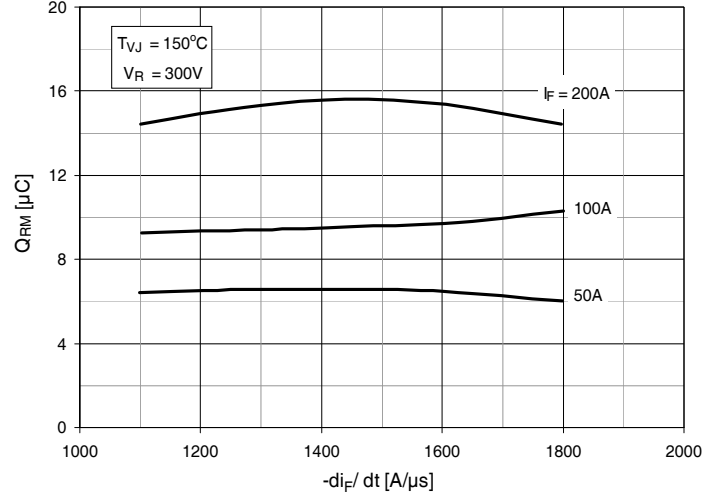


Fig. 23. Typ. Peak Reverse Current  $I_{RM}$  vs.  $-di_F/dt$

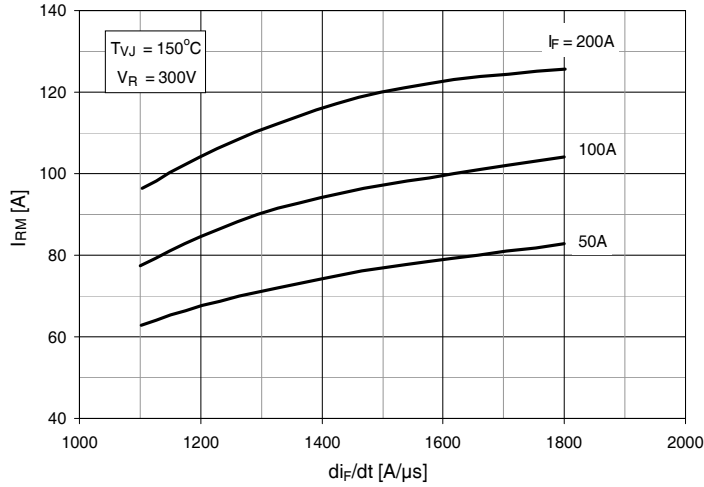


Fig. 24. Typ. Recovery Time  $t_{rr}$  vs.  $-di_F/dt$

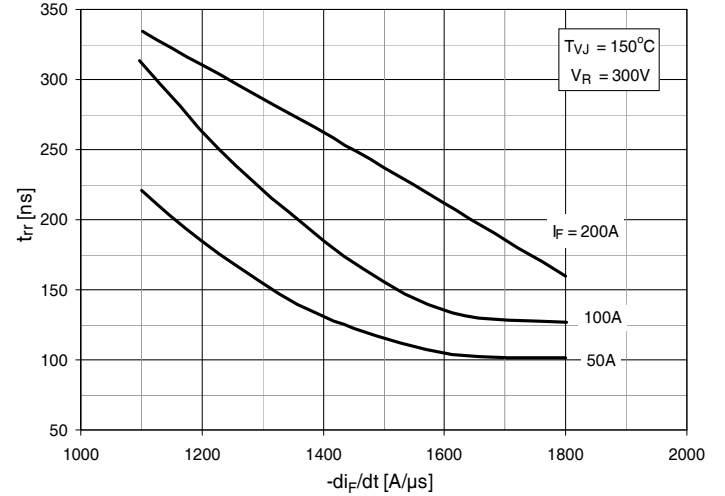


Fig. 25. Typ. Recovery Energy  $E_{rec}$  vs.  $-di_F/dt$

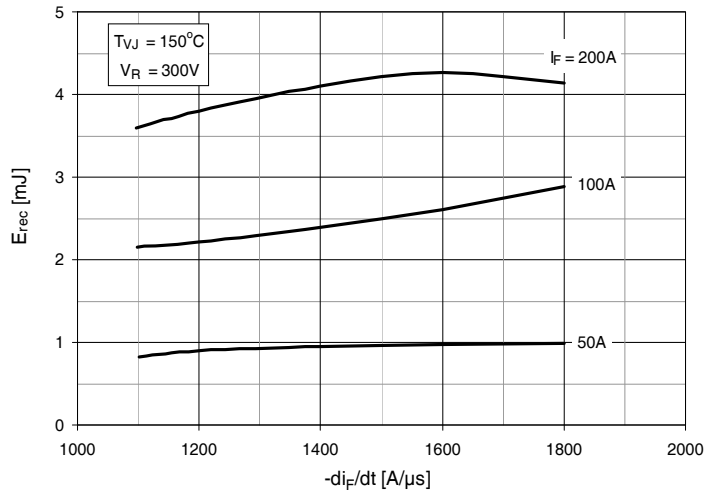
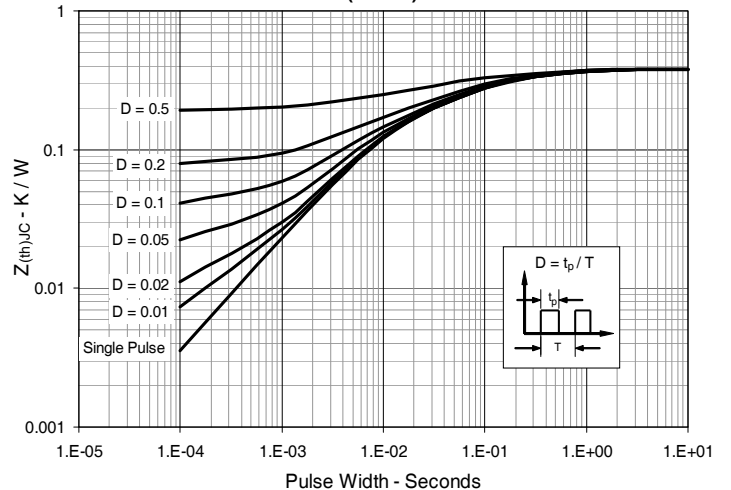
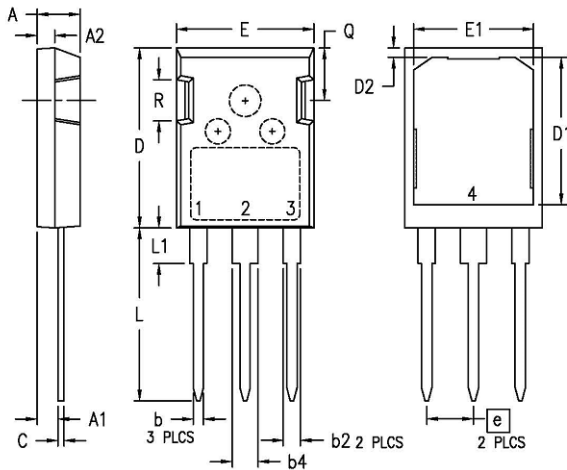


Fig. 26. Maximum Transient Thermal Impedance (Diode)

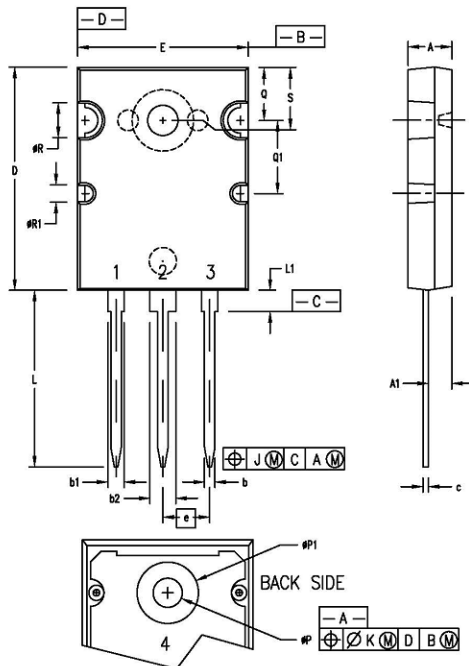


**PLUS247 Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.520	.560	13.08	14.22
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

PINS:  
 1 - Gate  
 2,4 - Collector  
 3 - Emitter

NOTE: 1. This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD (R-PSIP-F3) except screw mounting hole.  
 2. Pin #2 is connected to the bottom heatsink (#4).  
 3. Lead finish - One of the following depending on the packaging plants.  
 3.1 Matte pure tin plating on the leads and back heatsink.  
 3.2 Pb free solder dip on the leads and pre Ni plated back heatsink.

**TO-264 Outline**


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
ØP1	.270	.290	6.86	7.37
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PINS:  
 1 - Gate 2,4 - Collector  
 3 - Emitter

NOTE:  
 1. This drawing meets all dimensions requirement of JEDEC outlines TO-264AA.  
 2. Back heatsink is pre-Ni plated Cu.  
 3. Leads are Lead free solder dip unless specified as matte pure tin plating.





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).

---